

# PBHV8118T,215 Datasheet



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DiGi Electronics Part Number PBHV8118T,215-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number PBHV8118T,215

Description TRANS NPN 180V 1A TO236AB

Detailed Description Bipolar (BJT) Transistor NPN 180 V 1 A 30MHz 300 m

W Surface Mount TO-236AB



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## **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:			
PBHV8118T,215	Nexperia USA Inc.			
Series:	Product Status:			
	Active			
Transistor Type:	Current - Collector (Ic) (Max):			
NPN	1 A			
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:			
180 V	50mV @ 20mA, 100mA			
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:			
100nA	50 @ 500mA, 10V			
Power - Max:	Frequency - Transition:			
300 mW	30MHz			
Operating Temperature:	Grade:			
150°C (TJ)	Automotive			
Qualification:	Mounting Type:			
AEC-Q100	Surface Mount			
Package / Case:	Supplier Device Package:			
TO-236-3, SC-59, SOT-23-3	TO-236AB			
Base Product Number:				
PBHV8118				

## **Environmental & Export classification**

8541.21.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



## **PBHV8118T**

## 180 V, 1 A NPN high-voltage low VCEsat transistor

**Product data sheet** 

## 1. General description

NPN high-voltage low  $V_{CEsat}$  transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

#### 2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability  $\rm I_{C}$  and  $\rm I_{CM}$
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- Small SMD plastic package

### 3. Applications

- · LED driver for LED chain module
- LCD backlighting
- · Automotive power management
- · Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	180	V
I <sub>C</sub>	collector current		-	-	1	Α
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 10 V; $I_{C}$ = 50 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	100	250	-	



180 V, 1 A NPN high-voltage low VCEsat transistor

## 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	С
2	E	emitter		j
3	С	collector		В — (
				   E
			SOT23	sym021

## 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package						
	Name	Description	Version				
PBHV8118T	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23				

## 7. Marking

#### Table 4. Marking codes

Type number	Marking code[1]
PBHV8118T	LZ%

[1] % = placeholder for manufacturing site code

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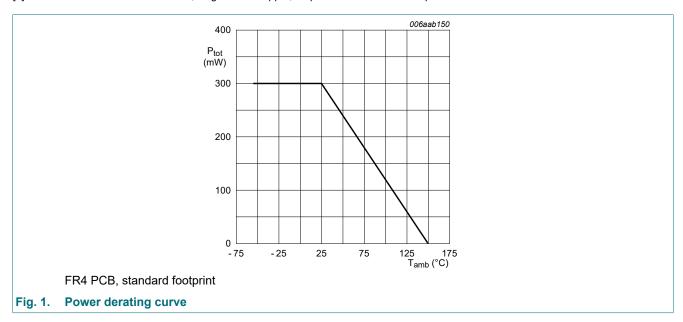
## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	400	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	180	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	6	V
Ic	collector current			-	1	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	2	Α
I <sub>BM</sub>	peak base current			-	400	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	300	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



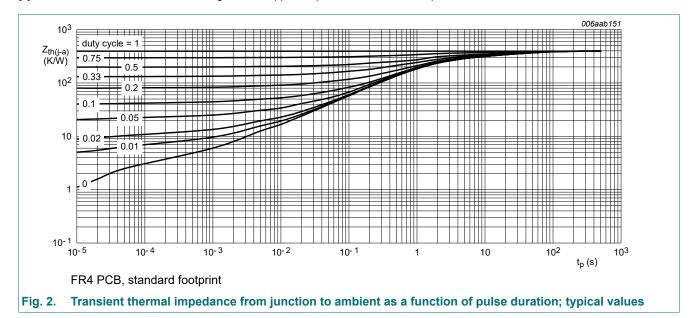
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#### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	70	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



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## 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = 144 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	V <sub>CB</sub> = 144 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	10	μΑ
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 144 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 4 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 10 V; $I_{C}$ = 50 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	100	250	-	
		$V_{CE}$ = 10 V; $I_{C}$ = 100 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	100	250	-	
		$V_{CE}$ = 10 V; $I_{C}$ = 0.5 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	50	100	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = 100 mA; $I_B$ = 10 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	40	60	mV
		$I_C$ = 100 mA; $I_B$ = 20 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	33	50	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C$ = 0.5 A; $I_B$ = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	1	1.2	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = 6 V; I <sub>C</sub> = 0.5 A; I <sub>Bon</sub> = 0.1 A;	-	7	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = -0.1 A; T <sub>amb</sub> = 25 °C	-	565	-	ns
t <sub>on</sub>	turn-on time		-	572	-	ns
t <sub>s</sub>	storage time		-	1320	-	ns
t <sub>f</sub>	fall time		-	740	-	ns
t <sub>off</sub>	turn-off time		-	2060	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = 10 V; $I_{C}$ = 10 mA; f = 100 MHz; $T_{amb}$ = 25 °C	-	30	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB}$ = 20 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C	-	5.7	-	pF
C <sub>e</sub>	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_{C} = 0 \text{ A}; i_{c} = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 ^{\circ}\text{C}$	-	150	-	pF

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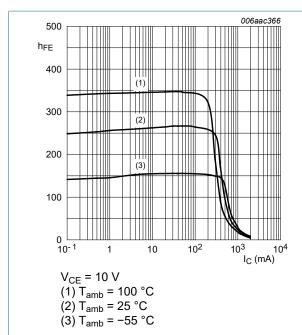


Fig. 3. DC current gain as a function of collector current; typical values

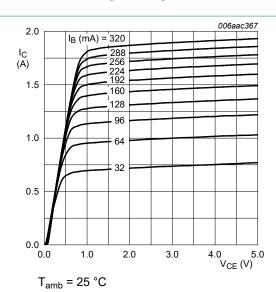


Fig. 4. Collector current as a function of collectoremitter voltage; typical values

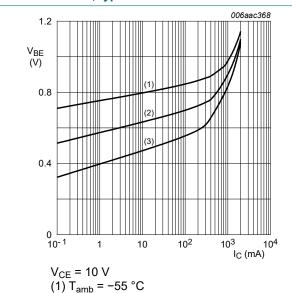
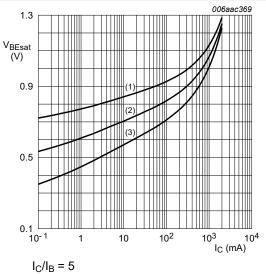


Fig. 5. Base-emitter voltage as a function of collector current; typical values

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3) T<sub>amb</sub> = 100 °C



 $I_C/I_B = 5$ (1)  $T_{amb} = -55$  °C (2)  $T_{amb} = 25$  °C (3)  $T_{amb} = 100$  °C

Fig. 6. Base-emitter saturation voltage as a function of collector current; typical values

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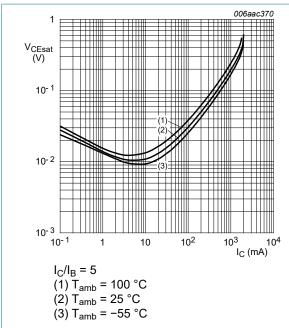


Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values

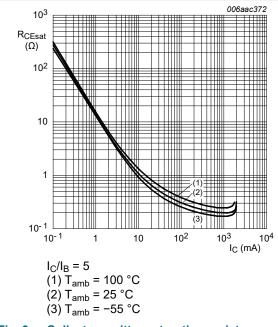


Fig. 9. Collector-emitter saturation resistance as a function of collector current; typical values

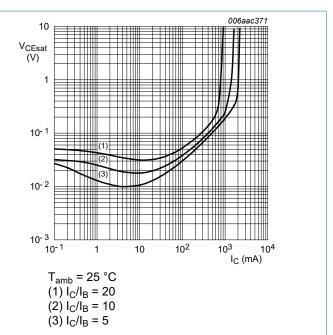


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

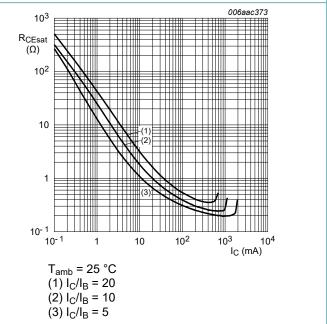
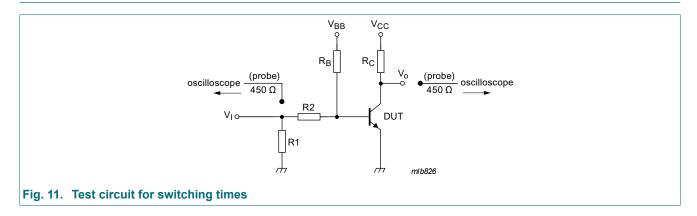


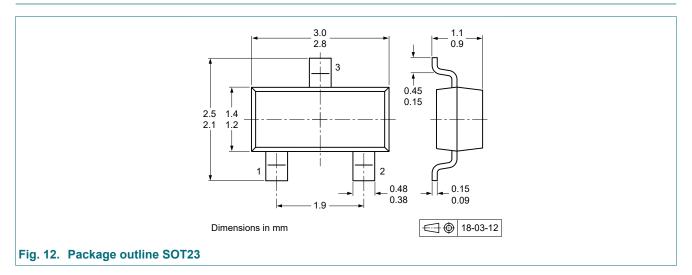
Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

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## 11. Test information

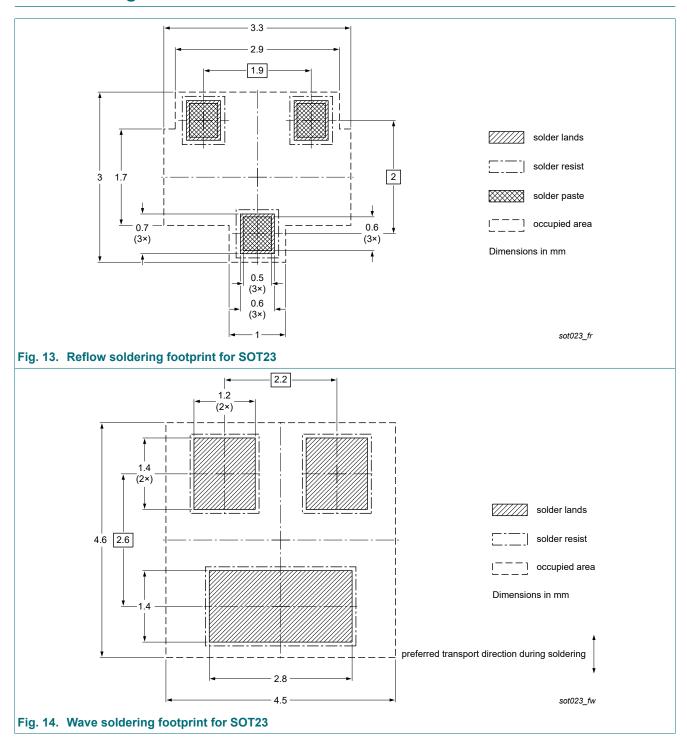


## 12. Package outline



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## 13. Soldering



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## 14. Revision history

#### **Table 8. Revision history**

Table of Novicion initially								
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PBHV8118T v.3	20241008	Product data sheet	-	PBHV8118T v.2				
Modifications:	<ul> <li>Product(s) changed to non-automotive qualification. Please refer to nexperia.com for automotive (-Q) product alternative(s).</li> </ul>							
PBHV8118T v.2	20230712	Product data sheet	-	PBHV8118T v.1				
PBHV8118T v.1	20100507	Product data sheet	-	-				

#### 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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